

TOSHIBA**2SA1425**

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

2SA1425

Power Amplifier Applications

Driver-Stage Amplifier Applications

Unit: mm

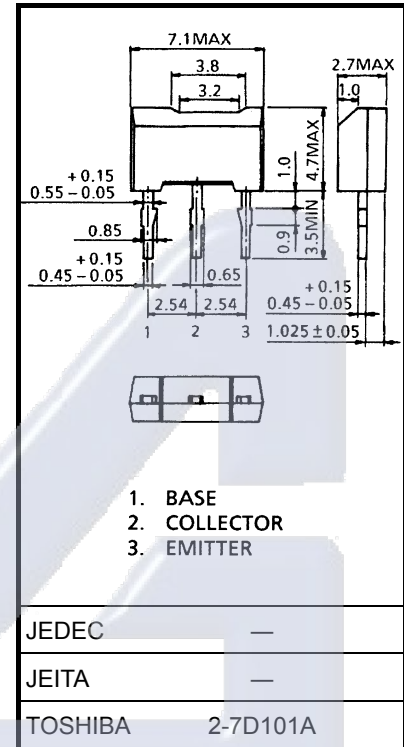
- Complementary to 2SC3665.

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-120	V
Collector-emitter voltage	V_{CEO}	-120	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-800	mA
Base current	I_B	-80	mA
Collector power dissipation	P_C	1000	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55 to 150	°C

Note1: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

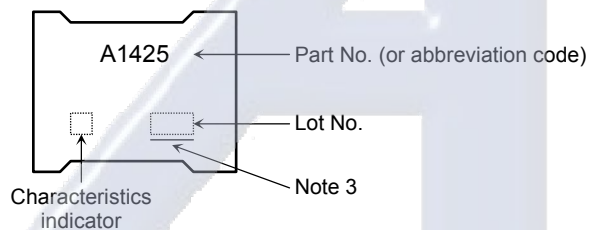


Weight: 0.2 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = -120\text{ V}, I_E = 0$	—	—	-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-100	nA
Collector-emitter breakdown voltage	$V_{(BR) CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-120	—	—	V
Emitter-base breakdown voltage	$V_{(BR) EBO}$	$I_E = -1\text{ mA}, I_C = 0$	-5	—	—	V
DC current gain	h_{FE} (Note 2)	$V_{CE} = -5\text{ V}, I_C = -100\text{ mA}$	80	—	240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{ mA}, I_B = -50\text{ mA}$	—	—	-1.0	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{ V}, I_C = -500\text{ mA}$	—	—	-1.0	V
Transition frequency	f_T	$V_{CE} = -5\text{ V}, I_C = -100\text{ mA}$	—	120	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	—	40	pF

Note 2: h_{FE} classification O: 80 to 160, Y: 120 to 240

Marking

Note 3: A line under a Lot No. identifies the indication of product Labels.

Not underlined: $[[Pb]]/INCLUDES > MCV$

Underlined: $[[G]]/RoHS\ COMPATIBLE$ or $[[G]]/RoHS\ [[Pb]]$

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

Electronica S.A. de C.V.

